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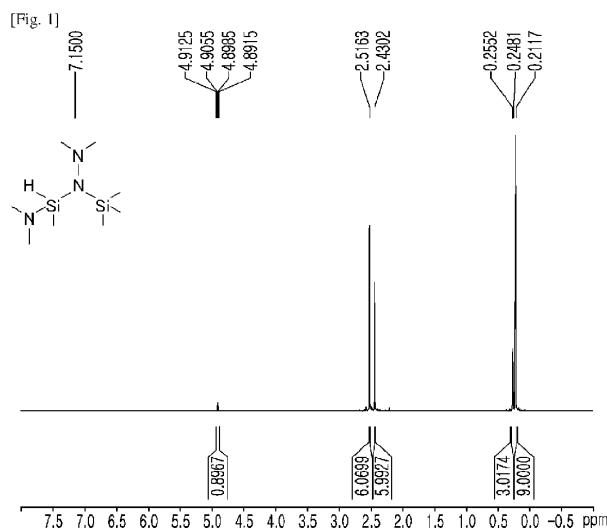
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(54) Title: SILICON PRECURSOR COMPOUND, METHOD FOR PREPARING THE SAME, AND METHOD FOR PREPARING
A SILICON-CONTAINING THIN FILM

(57) Abstract: The present invention relates to a novel silicon precursor compound capable of preparing an excellent silicon-containing thin film, to a method for preparing the same, and to a method for preparing a silicon-containing thin film using the silicon precursor compound. The silicon precursor compound of the present invention exhibits sufficient volatility to be applied to all of atomic layer deposition (ALD) and chemical vapor deposition (CVD) for preparing silicon-containing thin films. In particular, deposition is possible even at high temperatures in a high deposition rate, whereby a silicon-containing thin film with excellent quality can be prepared.

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